Form PTO 1449		U.S. DEPARTMENT	OF COMMERCE	ATTY DOCKET NO.		SERIAL NO.	
(Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		211147US99		09/903,784	
			APPLICANT				
LIST OF	REFE	RENCES CITED BY AP	PLICANT	Aroon V. TUNGARE, et al.			
				FILING DATE		GROUP	
			July 13, 2001		2826		
				U.S. PATENT DOCUMENTS			
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
PE	ZV	5,122,679	06/16/92	ISHII ET AL			
	zw	6,232,806	05/15/01	WOESTE ET AL			
1.	ZX	5,430,397	07/04/95	ITOH ET AL			
	ZY	6,151,240	11/21/00	SUZUKI			
	ZZ	6,528,374	03/04/03	BOJARCZUK, JR ET AL			
	A1	6,589,887	07/08/03	DALTON ET AL	Ì		
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1	A4	5,696,392	12/09/97	CHAR ET AL			
	A5	5,986,301	11/16/99	FUKUSHIMA ET AL			
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	1		FO	REIGN PATENT DOCUMENTS	L	L	
	DOCUMENT DATE		COUNTRY		TRANSLATION		
		NUMBER				YES	S NO
Po	ccs	WO 99/67882	12/29/99	WIPO			
	ССТ	WO 95/02904	01/26/95	WIPO			
	ccu	WO 02/009150	01/31/02	WIPO			
	ccv	0 766 292	04/02/97	EUROPE			
	ccw	198 29 609	01/05/00	GERMANY			
	ccx	1 069 605	01/17/01	EUROPE			
	CCY	0 828 287	03/11/98	EUROPE			
	ccz	1 176 230	01/30/02	EUROPE			
		OTHER RE	FERENCES (Including Author, Title, Date, Pertinent	Pages, e	tc.)	-
YI W. et al; "Mechanism of cleaning Si (100) surface using Sr and SrO for the growth of crystalline SrTiO/sub 2/films" Journal							
16	LLAP	of Vacuum Science & Technology, Vol. 20, No. 4, July 2002 (2002-07) pp. 1402-1405					
Pe	LLAQ	XIAMING HU et al; "Sr/Si template formation for the epitaxial growth of SrTiO/sub 3/on silicon" Materials Research Society Proceedings, Vol. 716, 2002, pp. 261-266					
·	LLAR						
LLAS				Additional References sheet(s) attached			
Examiner Date Considered 10/30/01							
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant							
i comomance	and v o	a considered. Include co	nov or this tom	i willi nexi communication to applicant			